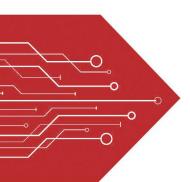
## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet







**SOT - 23** 



1. BASE

2. EMITTER

3. COLLECTOR

#### **FEATURES**

Ideally suited for automatic insertion For switching and AF amplifier applications

#### **DEVICE MARKING**

P/N	MARK	P/N	MARK	P/N	MARK
BC846A	1A	BC847A	1E	BC848A	1J
BC846B	1B	BC847B	1F	BC848B	1K
BC846C	1C	BC847C	1G	BC848C	1L

#### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage		V
	BC846	80	
	BC847	50	
	BC848	30	
V <sub>CEO</sub>	Collector-Emitter Voltage		V
	BC846	65	
	BC847	45	
	BC848	30	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ic	Collector Current –Continuous	0.1	Α
Pc	Collector Power Dissipation	200	mW
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	℃

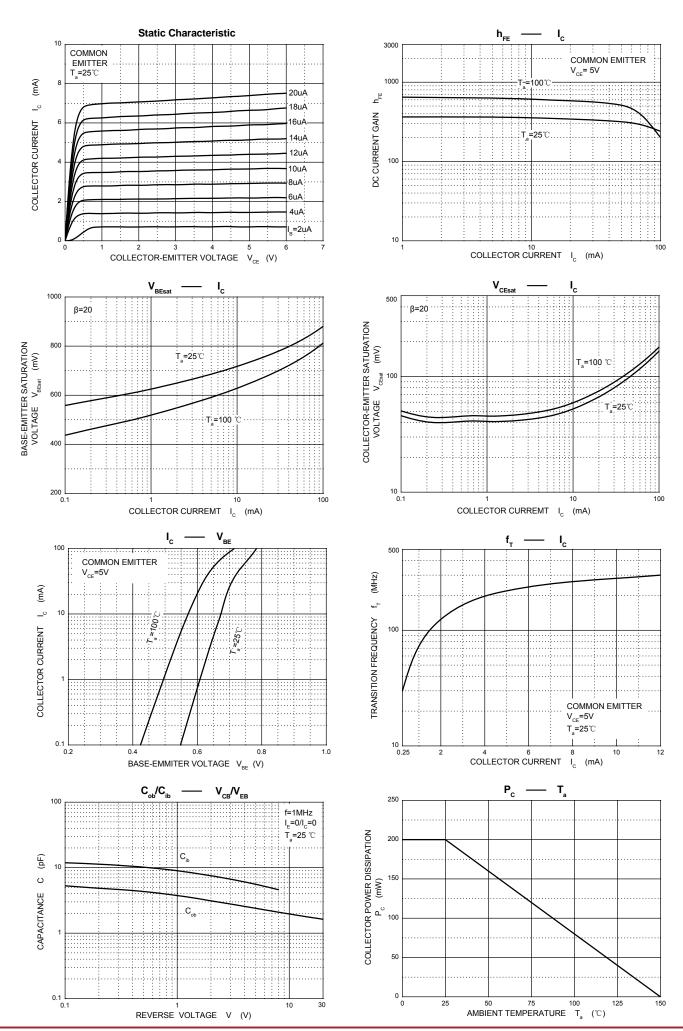






#### **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

Parameter		Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	BC846			80			
	BC847	$V_{CBO}$	I <sub>C</sub> = 10μΑ, I <sub>E</sub> =0	50			V
	BC848			30			
Collector-emitter breakdown voltage	BC846			65			
	BC847	$V_{\text{CEO}}$	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	45			V
	BC848			30			
Emitter-base breakdown voltage		$V_{EBO}$	I <sub>E</sub> = 10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	BC846		V <sub>CB</sub> =70 V , I <sub>E</sub> =0				
	BC847	$I_{CBO}$	$V_{CB}$ =50 V , $I_{E}$ =0			0.1	μΑ
	BC848		$V_{CB}$ =30 V , $I_{E}$ =0				
Collector cut-off current	BC846		V <sub>CE</sub> =60 V , I <sub>B</sub> =0				
	BC847	I <sub>CEO</sub>	V <sub>CE</sub> =45 V , I <sub>B</sub> =0			0.1	μΑ
	BC848		$V_{CE}$ =30 V , $I_{B}$ =0				
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> =5 V , I <sub>C</sub> =0			0.1	μA
DC current gain B0	C846A,847A,848A			110		220	
ВС	C846B,847B,848B	$h_{FE}$	$V_{CE}$ = 5V, $I_{C}$ = 2mA	200		450	
BC8460	,BC847C,BC848C			420		800	
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> =100mA, I <sub>B</sub> = 5mA			0.5	V
Base-emitter saturation voltage		V <sub>BE</sub> (sat)	I <sub>C</sub> =100mA, I <sub>B</sub> = 5mA			1.1	V
Transition frequency		f⊤	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10mA f=100MHz	100			MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> =10V,f=1MHz			4.5	pF

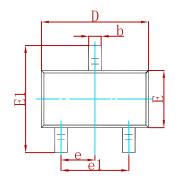


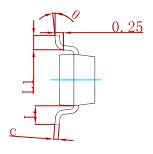


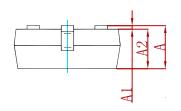




#### **PACKAGE MECHANICAL DATA**

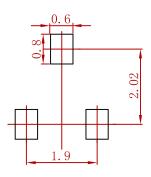






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BC846/BC847/BC848	SOT-23	3000





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